















**ESD** 

TVS

MOS

LDO

Diode

Sensor

DC-DC

# **Product Specification**

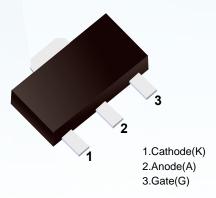
Domestic Part Number	MCR100-4/-6/-8
Overseas Part Number	MCR100-4/-6/-8
▶ Equivalent Part Number	MCR100-4/-6/-8





### Silicon Controlled Rectifiers

- Features
- Sensitive gate silicon controlled rectifiers
- Reverse blocking thyristors



## ■ Simplified outline(SOT-89)

Pin	Symbol	Description		
1	K	Cathode		
2	А	Anode		
3	G	Gate		

### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbols	Value	Units	
Peak Repetitive Off-State Voltage Note4	MCR100-4		200	
$(T_J = -40$ °C to 110°C, Sine Wave, 50 to 60 Hz,	MCR100-6	$V_{DRM}, V_{RRM}$	400	V
Gate Open)	MCR100-8		600	
On-State RMS Current		I <sub>T(RMS)</sub>	0.8	А
Peak Non-Repetitive Surge Current		8	^	
(1/2 Cycle, Sine Wave, 60 Hz, T <sub>J</sub> = 25°C)	I <sub>TSM</sub>	0	A	
Circuit Fusing Considerations (t = 8.3ms)		l <sup>2</sup> t	0.415	A <sup>2</sup> s
Forward Peak Gate Power (Pulse Width ≤ 1 µs)		$P_GM$	0.1	W
Forward Average Gate Power (t = 8.3ms)		$P_{G(AV)}$	0.1	W
Peak Gate Current – Forward (Pulse Width ≤ 1 µs)		I <sub>GM</sub>	1	Α
Peak Gate Voltage – Reverse (Pulse Width ≤ 1 µs)		$V_{GRM}$	5	٧
Operating Junction Temperature Range		TJ	- 40 to + 110	°C
Storage Temperature Range		T <sub>STG</sub>	- 40 to + 150	°C



### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbols	Max.	Units	
Peak Forward or Reverse Blocking Current Note: at $V_D$ = Rated $V_{DRM}$ and $V_{RRM}$ , $R_{GK}$ =1 $K\Omega$	2	I <sub>DRM</sub> , I <sub>RRM</sub>	10	μА
Peak Forward On-State Voltage <sup>Note1</sup> at I <sub>TM</sub> = 0.8 A		V <sub>TM</sub>	1.7	V
Gate Trigger Current $^{Note3}$ at $V_{AK}$ = 7 V, $R_L$ = 100 $\Omega$		I <sub>GT</sub>	200	μА
Holding Current Note2 at V <sub>AK</sub> = 7 V, Initiating Current = 20 mA	T <sub>C</sub> = 25°C T <sub>C</sub> =- 40°C	I <sub>H</sub>	5 10	mA
Latch Current at V <sub>AK</sub> = 7 V, I <sub>g</sub> = 1 mA	T <sub>C</sub> = 25°C T <sub>C</sub> = - 40°C	I <sub>L</sub>	10 15	mA
Gate Trigger Voltage <sup>Note3</sup> at $V_{AK}$ = 7 V, $R_L$ = 100 $\Omega$	T <sub>C</sub> = 25°C T <sub>C</sub> = - 40°C	VgT	0.8 1.2	V

#### Note:

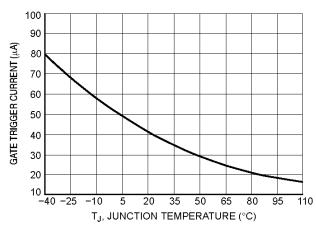
<sup>1)</sup>Indicates pulse teat width  $\leq$  1 ms, duty cycle  $\leq$ 1%

<sup>2)</sup>RGK = 1 K $\Omega$  included in measurement

<sup>3)</sup>Does not include RGK in measurement

<sup>4)</sup>VDRM and VRRM for all types can be applied on continous basis. Ratings apply for zero negative gate voltage; however,positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

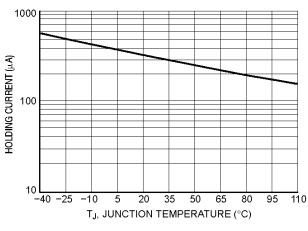




1.0 0.9 GATE TRIGGER VOLTAGE (VOLTS) 0.8 0.7 0.6 0.5 0.4 0.3 0.2 <del>-40 -25</del> 20 35 50 65  $T_J$ , JUNCTION TEMPERATURE (°C)

Figure 1. Typical Gate Trigger Current versus
Junction Temperature

Figure 2. Typical Gate Trigger Voltage versus Junction Temperature



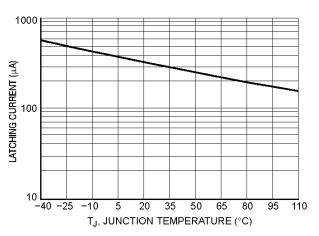
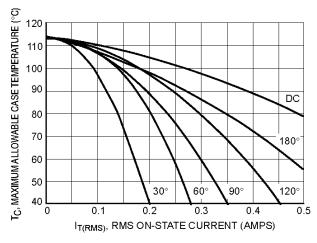


Figure 3. Typical Holding Current versus Junction Temperature

Figure 4. Typical Latching Current versus Junction Temperature



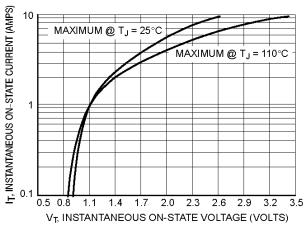
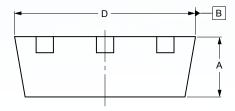


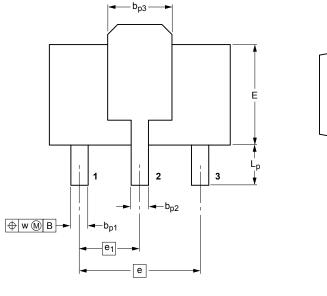
Figure 5. Typical RMS Current Derating

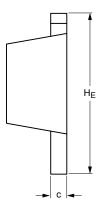
Figure 6. Typical On-State Characteristics



### ■ SOT-89









#### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	b <sub>p1</sub>	b <sub>p2</sub>	b <sub>p3</sub>	С	D	E	е	e <sub>1</sub>	HE	Lp	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13



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